

ASC60N1200MT3

1200V N-Channel MOSFET

Description

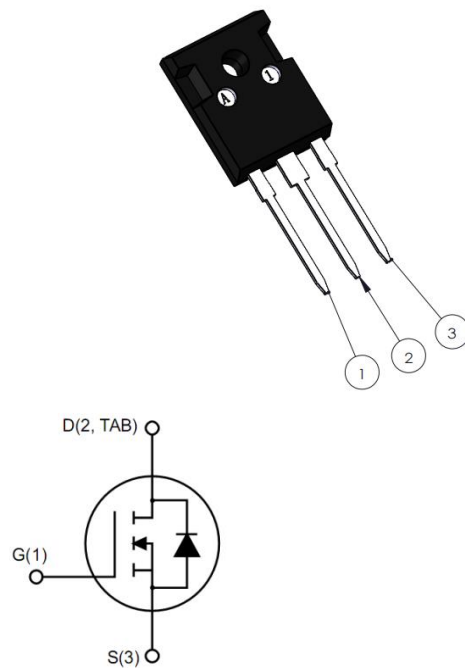
Silicon Carbide (SiC) MOSFET use a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size.

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low RDS(on)
- Easy to parallel and simple to drive
- ROHS Compliant, Halogen free

Application

- EV motor drive
- High Voltage DC/DC Converters
- Switch Mode Power Supplies
- Solar inverters
- EV charging



Ordering Information

Part Number	Marking	Package	Packaging
ASC60N1200MT3	ASC60N1200MT3	TO-247-3	Tube

Absolute Maximum Ratings(Tc=25°C)

Symbol	Parameter	Value	Unit
V _{DS}	Drain-Source Voltage	1200	V
I _D	Drain Current(continuous)at Tc=25°C	60	A
I _D	Drain Current(continuous)at Tc=100°C	48	A
I _{DM}	Drain Current (pulsed)	100	A
V _{GS}	Gate-Source Voltage	-10/+22	V
P _D	Power Dissipation T _C = 25°C	395	W
T _J , Tstg	Junction and Storage Temperature Range	-55 to +175	°C

Electrical Characteristics(T_J = 25°C unless otherwise specified)

Typical Performance-Static

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DS}	Drain-source Breakdown Voltage	I _D =250uA, V _{GS} =0V	1200			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =1200V, V _{GS} =0V, T _J =25°C			100	uA
I _{GSS}	Gate-body Leakage Current	V _{DS} =0V ; V _{GS} =-10 to 20V			250	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =10mA	2	3	4	V
V _{GS(on)}	Recommended turn-on Voltage	Static		18		V
V _{GS(off)}	Recommended turn-off Voltage			-5		V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} =18V, I _D =20A		45	52	mΩ
		V _{GS} =18V, I _D =20A T _J =175°C		81		mΩ

Typical Performance-Dynamic

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS}=1000V, f=100kHz,$ $V_{AC}=25mV$		2565		pF
C_{oss}	Output Capacitance			109		pF
C_{rss}	Reverse Transfer Capacitance			4		pF
g_{fs}	Transconductance	$V_{DS}=20V, I_D=20A$		24		S
E_{OSS}	C_{OSS} Stored Energy	$V_{DS}=1000V, f=100kHz$		63		μJ
E_{ON}	Turn-On Energy (Body Diode)	$V_{DS}=800V, V_{GS}=-5/20V,$ $I_D=20A, L=100\mu H$ $T_J=175^\circ C$		1695		μJ
E_{OFF}	Turn-Off Energy (Body Diode)			306		μJ
Q_g	Total Gate Charge	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D=20A$		125		nC
Q_{gs}	Gate-source Charge			32		nC
Q_{gd}	Gate-Drain Charge			33		nC
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		4.2		Ω
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=800V, V_{GS}=-5V/20V,$ $I_D=20A, L=100\mu H$ $R_{ext}=2.5\Omega$		17		ns
t_r	Rise Time			66		ns
$t_{d(off)}$	Turn-off Delay Time			28		ns
t_f	Fall Time			14		ns

Typical Performance-Reverse Diode($T_J = 25^\circ C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{FSD}	Forward Voltage	$V_{GS}=0V, I_F=20A, T_J=25^\circ C$		4.2	6	V
		$V_{GS}=0V, I_F=20A, T_J=175^\circ C$		3.5	6	V
I_S	Continuous Diode Forward Current	$V_{GS}=0V, T_C=25^\circ C$		55		A
t_{rr}	Reverse Recovery Time	$V_{GS}=-5V, I_F=20A,$ $V_R=800V, di/dt=900$ $A/\mu s, T_J=175^\circ C$		50		nS
Q_{rr}	Reverse Recovery Charge			712		nC
I_{rrm}	Peak Reverse Recovery Current			19		A

Thermal Characteristics

Symbol	Parameter	Value.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.38	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	40	$^\circ C/W$

The values are based on the junction-to case thermal impedance which is measured with the device mounted to a large heat sink assuming maximum junction temperature of $T_J(max)=175^\circ C$

Electrical Characteristics

Fig1. Output characteristics ($T_J = 25^\circ\text{C}$)

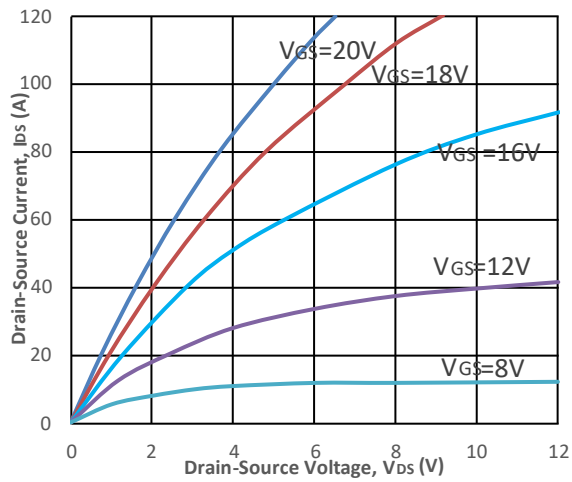


Fig2. Output characteristics ($T_J = 175^\circ\text{C}$)

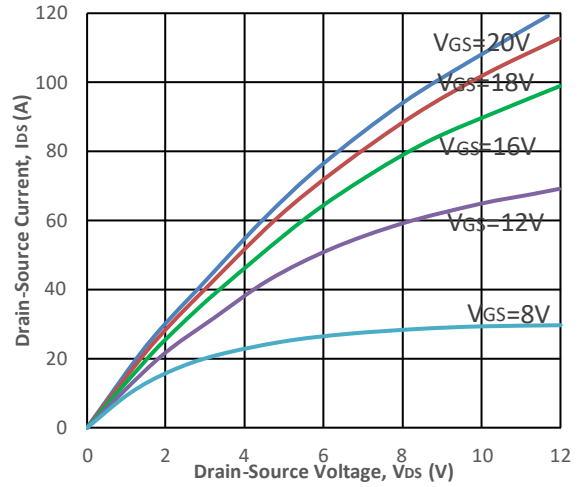


Fig3. Normalized On-Resistance vs. Temperature

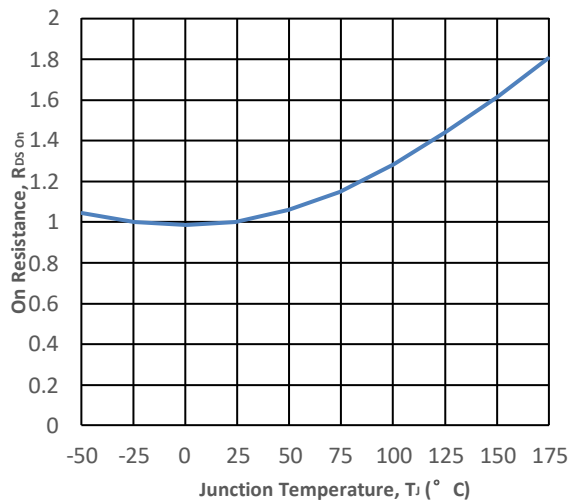


Fig4. On-Resistance vs. Temperature

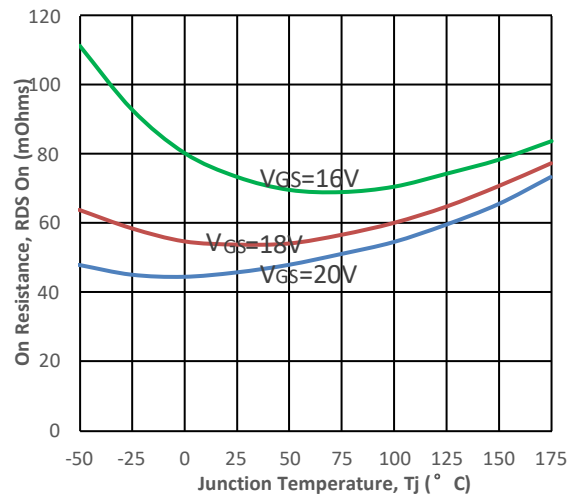


Fig5. Transfer Characteristic

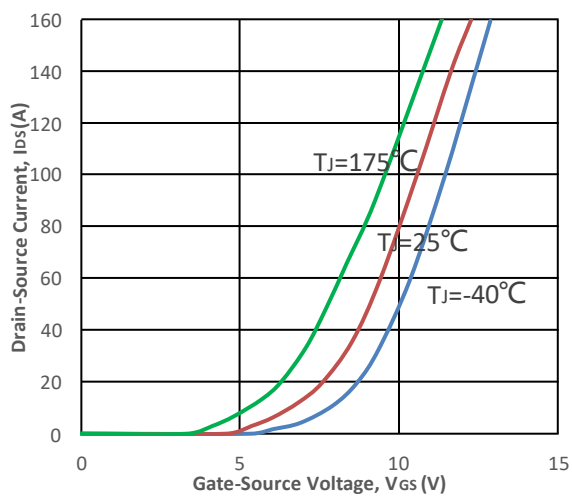


Fig6. Body Diode Characteristic at 25°C

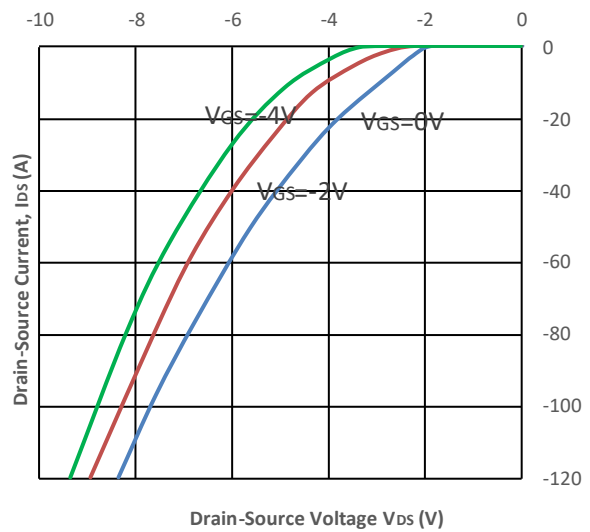


Fig7.Threshold Voltage vs. Temperature

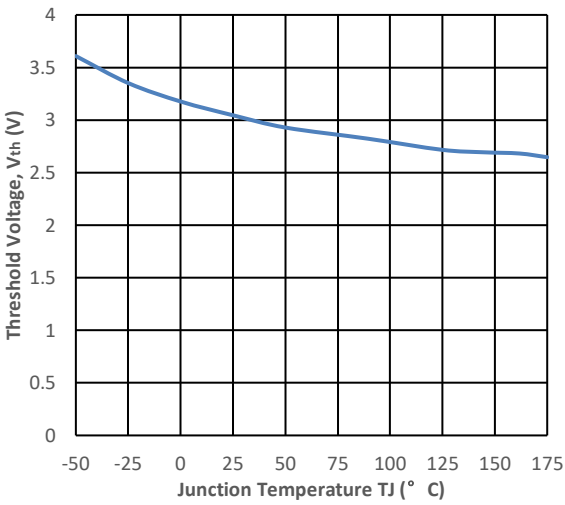


Fig8. Gate Charge Characteristics

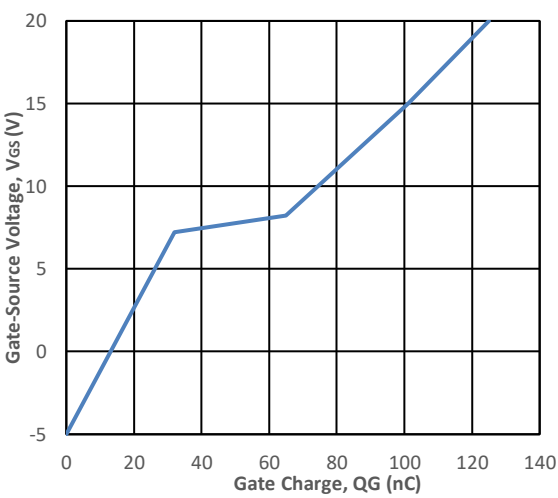


Fig9. 3rd Quadrant Characteristic at 25 $^{\circ}C$

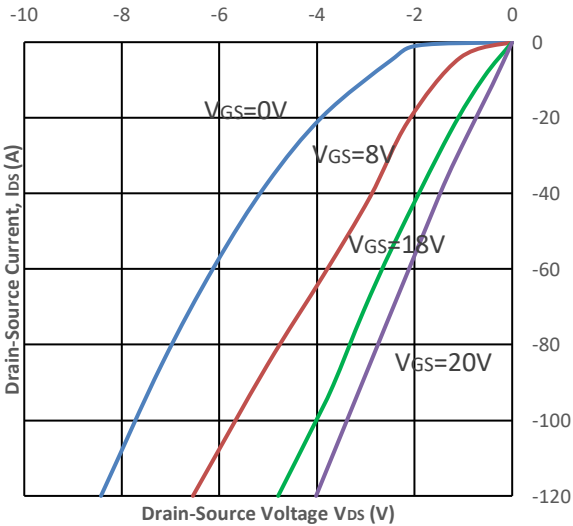


Fig10. Output Capacitor Stored Energy

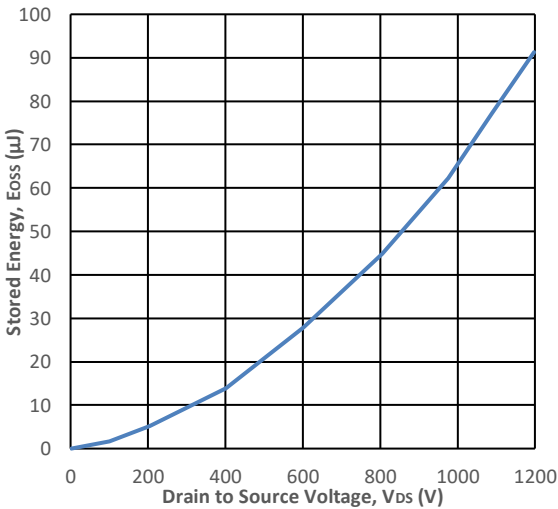


Fig11. Capacitances vs. Drain-Source

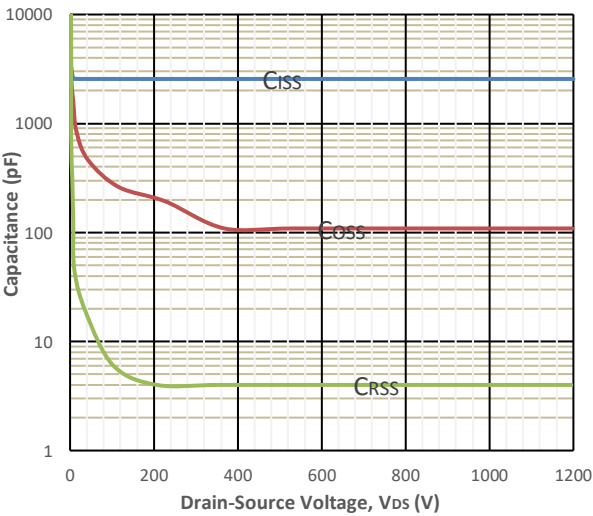


Fig12. Max Power Dissipation Derating Vs T_c

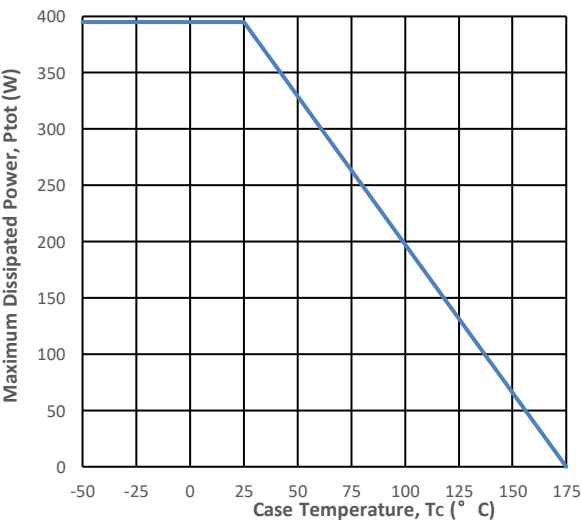


Fig13. Switching Energy vs. Drain Current

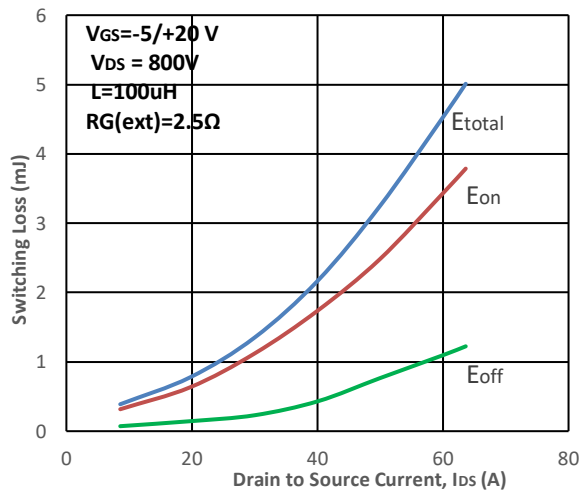


Fig14. Switching Energy vs. $R_{G(ext)}$

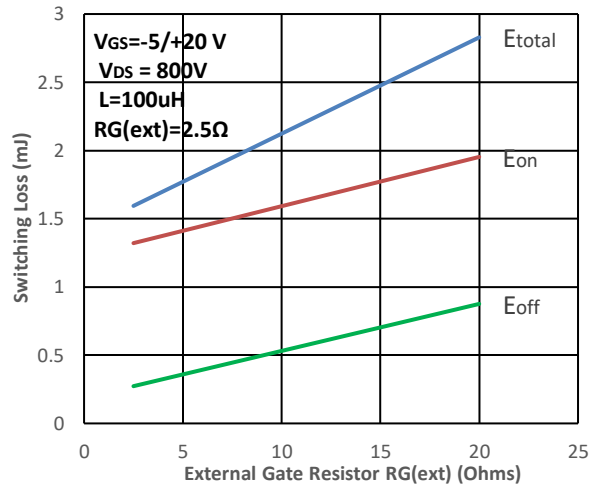


Fig15. Switching Energy vs. Temperature

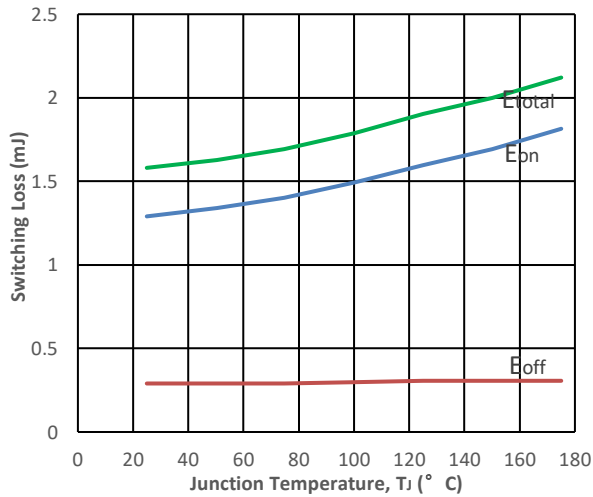


Fig16. Switching Times vs. $R_{G(ext)}$

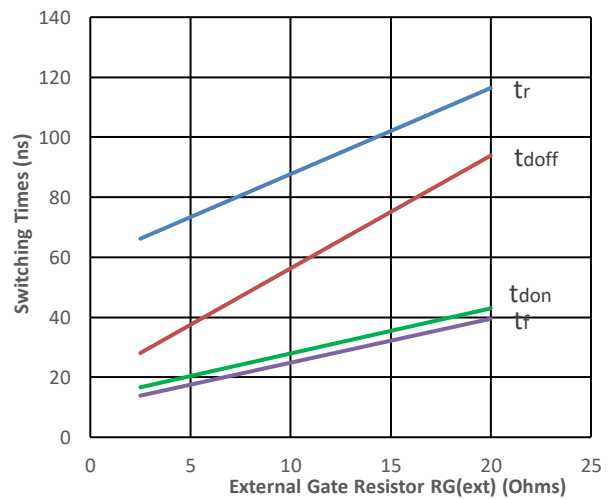


Fig17. Transient Thermal Impedance

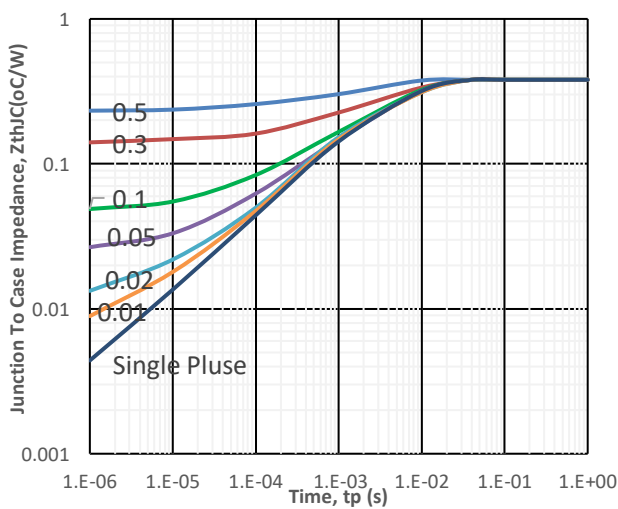
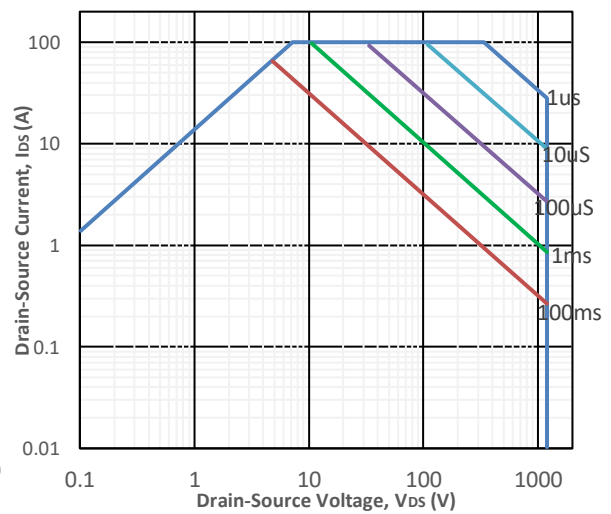
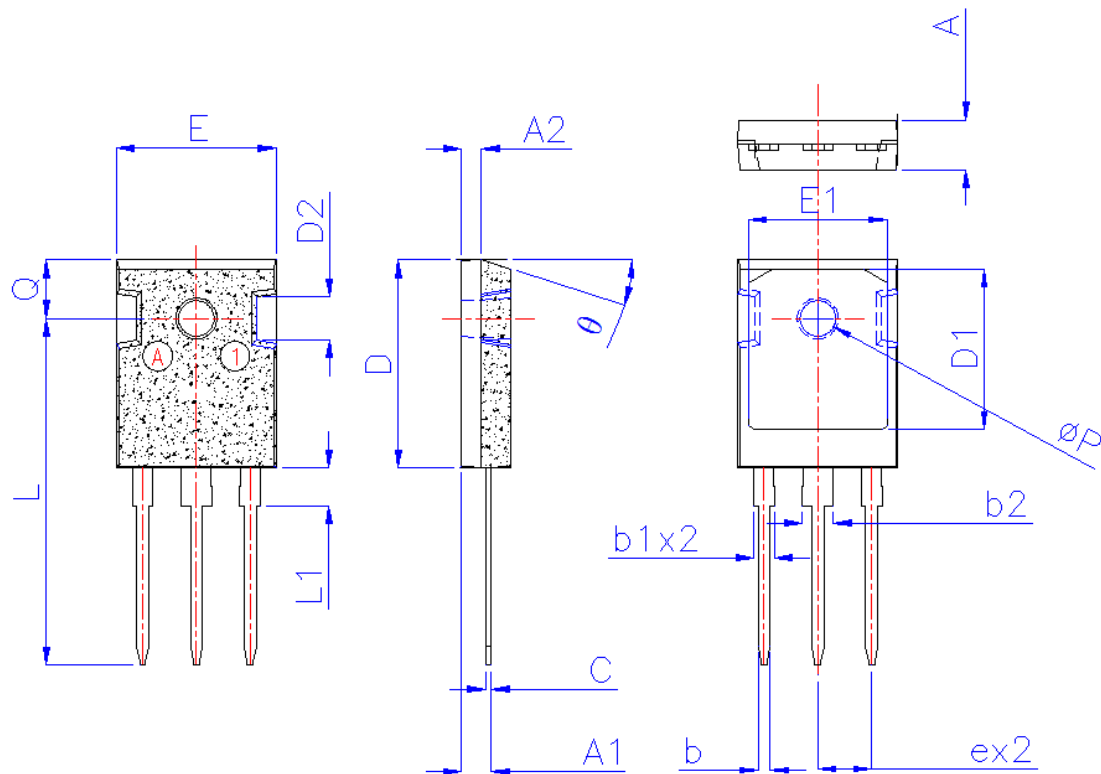


Fig18. Safe Operating Area



Package Drawing:



Dimensions (UNIT: mm)

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	TYPE	MAX	MIN	TYPE	MAX
A	4.80	5.00	5.20	0.189	0.197	0.205
A1	2.85	3.00	3.15	0.112	0.118	0.124
b	1.16	1.22	1.27	0.046	0.048	0.050
b1	2.03	2.06	2.10	0.080	0.081	0.083
b2	3.03	3.06	3.10	0.119	0.120	0.122
C	0.55	0.60	0.65	0.022	0.024	0.026
D	20.80	21.00	21.20	0.819	0.827	0.835
D1	15.94	16.24	16.54	0.628	0.639	0.651
D2	4.30 BSC			0.169 BSC		
e	5.44 BSC			0.214 BSC		
E	15.95	16.15	16.35	0.628	0.636	0.644
E1	13.82	14.02	14.26	0.544	0.552	0.561
L	34.65	35.05	35.45	1.364	1.380	1.396
L1	—	—	3.86	—	—	0.152
Q	5.85	5.95	6.05	0.230	0.234	0.238
øP	3.45	3.60	3.75	0.136	0.142	0.148
θ	17.5°			0.689°		

Notes:

- The information in this document is subject to change without notice.
- For more product and company information, please contact us or visit the website.

Contact Info:

- Tel: +86 13510099916
- Web: www.ewsemi.com



专注

Focus

品质

Quality

创新

Innovation

共赢

Win-win

